

***Optical and electrical properties of Pb(Te,S) nanomaterials
prepared by hydrothermal method for
application in solar cells***

A thesis submitted by

Eman Mohamed El-hanafy Abo El-Ekhlal

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Supervisors

Prof. Dr. Hayam Abd- El Aziz El-Zahed

Ass. Prof. Gehan Mohamed Mahmoud

Ass. Prof. Emad El-Din Mohamed El-Menyawy

Ass. Prof. Ali Ahmed Mohamed Azab

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Ass. Prof. Emad El-Din Mohamed El-Menawy

Ass. Prof. Ali Ahmed Mohamed Azab

Referees

Prof. Dr. Mohamed Mouner Sad El-Din

Prof. of Solid State Physics, Physics Dept., Science college, Cairo University

Prof. Dr. Seham Mahmoud Salem

Prof. of Solid State Physics, Physics Division, National Research Center

Prof. Dr. Hayam Abd- El Aziz El-Zahed,

Prof. of Solid State Physics, Physics Department, Faculty of Women for Arts, Science and Education, Ain Shams University

Ass. Prof. Dr. Gehan Mohamed Mahmoud

Ass. Prof. of Solid State Physics, Physics Division, National Research Center

Approval Sheet

Student name: Eman Mohamed El_Hanafy Abo El_Ekhlal

Scientific degree: Ph.D. in solid state physics

Faculty: Faculty of Women, Arts, science and Education

Department: Physics department

University: Ain Shams University

Degree awarded: M. Sc. In Solid State Physics



To

My dear husband,

my parents,

my kind sons and daughter

and my family

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Contents

Chapter 1.Introduction and Literature Review

1.1 Introduction.....	1
1.2 The aim of the present work	12
1.3 Literature review	13

Chapter 2 Theoretical Consideration

2.1. Introduction.....	27
2.2. Energy bands and electrical conduction.....	27
2.3. Semiconductors.....	29
2.4. Electrical transport properties of semiconductors.....	30
2.4.1.Electrical conductivity of semiconductors.....	30
2.4.2.Hall effect.....	31
2.5. Optical properties of semiconductors.....	35
2.5.1.Fundamental absorption.....	35
2.6. Electron diffraction theory.....	36
2.7. Nanotechnology.....	39
2.8. Nanomaterials	40
2.9. Quantum confinement effect.....	41
2.10. Size-dependent properties of semiconducting nanostructure.....	43
2.11. P-N Junctions.....	44

Chapter 3 Experimental techniques and measurements

3.1. Introduction.....	48
3.2. Preparation of PbS and PbTe by hydrothermal method.....	49
3.3.A.c. Measurements.....	50
3.4. Thin film preparation.....	51
3.4.1. Thermal vacuum evaporation.....	52
3.5. Film thickness determination.....	52
3.5.1 Interferometric methods.....	53
3.6. Characterization.....	55
3.6.1. Energy dispersive X-ray spectroscopy.....	55
3.6.2. X-ray diffraction techniques.....	56

3.6.3. Grazing incidence X-ray diffraction technique	57
3.6.4. Transmission electron microscope (TEM).....	57
3.7. Optical measurements.....	58
3.8. Electrical measurements.....	59
3.9. Current – voltage characteristics.....	61

Chapter 4 Structural results

4.1. Introduction.....	62
4.2. Structural results of PbS and PbTe bulk nanomaterials.....	62
4.2.1. X-ray diffraction results o PbS and PbTe nanomaterials.....	62
4.2.2. Scanning Electron Microscopy (SEM) results of powdered nanomaterials..	66
4.3. Structural results of PbS and PbTe nanocrystalline films.....	68
4.3.1. X-ray diffraction results of PbS and PbTe films.....	68
4.3.2. Quantitative compositional analysis (EDX).....	70
4.4. Transmission Electron Microscopy results of PbS and PbTe films.....	74

Chapter 5 Optical properties of thin films

5.1. PbS optical properties.....	99
5.2. PbTe optical results.....	112

Chapter 6 Electrical results

6.1. A.C. Electrical results of PbS and PbTe bulk nanomaterial.....	121
6.1.1. AC Conductivity.....	121
6.1.2. Dielectric properties.....	125
6.1.3. Electric modulus spectrum.....	130
6.2. Electrical properties of PbS and PbTe thin films.....	136
6.2.1. Electrical properties of PbTe thin films.....	136

6.2.2. PbS electrical results.....	141
6.3. Current – voltage characteristics of heterojunctions.....	144
6.3.1. Current – voltage characteristics of Au/p-PbS/n-Si/Al heterojunction.....	144
6.3.2. Current – voltage characteristics of Au/p-PbTe/n-Si/Al heterojunction.....	154
Conclusions.....	161
References.....	166

List of figures

Fig. 1.1 . The crystal structure of PbS and PbTe.

Fig. 1.2. Band structures of PbS, and PbTe as reported by Delin et al. [9].

Fig. 2.1 Metal, semiconductor and insulator.

Fig. 2.2 Schematic of specimen is showing dimensions and direction of axes.

Fig. 2.3 Schematic representation of electron diffraction theory.

Fig. 2.4 X - ray diffraction pattern and the electron diffraction patterns of polycrystalline aluminum.

Fig. 2.5 Electronic state diagram showing the quantum confinement effect (a) bulk semiconductors and (b) nanoparticles.

Fig. 2.6 Relation between the density of states and the energy for bulk material, quantum well, quantum wire and quantum dot.

Fig. 2.7 Blue shift in the band energy due to confinement nm -sized with respect to the bulk crystal.

Fig. 3.1 Teflon – coated autoclave.

Fig. 3.2 Coating unit model Edwards E 306 A.

Fig. 3.3 A schematic diagram of the optical interference microscope used for film thickness measurements.

Fig. 3.4 Optical interference microscope used for roughness measurements.

Fig. 3.5 A schematic diagram for Bragg's Law.

Fig. 3.6 Schematic diagram for the influence of electric and magnetic field on the sample.

Fig. 3.7 A schematic diagram for the sample.

Figs. 4.1 (a and b) The XRD patterns of the prepared PbS and PbTe powdered nanomaterials.

Fig.4.2 (a and b) SEM micrographs of PbS nanomaterial.

Fig.4.3 (a and b) SEM micrograph of our prepared PbTe nanomaterial.

Fig.4.4 X-ray diffraction of PbS films.

Fig.4.5 X-ray diffraction of PbTe films.

Fig.4.6 EDX pattern of PbS nanomaterial powder and PbS nanomaterial films with different thicknesses: 26 nm, 34 nm, 79 nm and 93 nm.

Fig.4.7 EDX pattern of PbTe powdered nanomaterial, and PbTe films with different thicknesses 21, 50 and 66 nm.

Fig.4.8 The TEM results of PbS films of thicknesses 26, 34, 79 and 93 nm.

Fig. 4.9 Statistical distribution of PbS films of thicknesses 26,34,79 and 93 nm

Fig. 4.10 Relationship between the average crystallite size and film thickness.

Fig. 4.11 The HRTEM lattice fringes inside the nanoparticles for PbS film thicknesses 26, 34, 79 and 93 nm.

Fig. 4.12 Selected Area- Electron Diffraction ,SAED for PbS films thicknesses 26, 34, 79 and 93 nm.

Fig.4.13 TEM results of PbTe films of thicknesses 21, 50 and 66 nm.

Fig.4.14 Statistical distribution of particle size for PbTe films of thicknesses 21, 50 and 66 nm.

Fig.4.15 Variation of the average crystallite size of PbTe thin films with film thickness.

Fig. 4.16 HRTEM micrograph of lead telluride films of thicknesses 21, 50 and 66 nm, showing the lattice fringes..

Fig. 4.17 Electron diffraction of PbTe films of thicknesses 21, 50 and 66 nm respectively.

Fig. 5.1 The optical transmittance and reflectance spectra of PbS nanocrystalline films with thickness values 26, 34, 79 and 93 nm.

Fig. 5.2 The relationship between the absorption coefficient, α , and the wavelength.

Fig.s 5.3 Relationships between $(\alpha h\nu)^2$ and the photon energy, $h\nu$.

Fig. 5.4 The relation between the optical energy gap and the average particle size for PbS films

Fig.5.5 The spectral distribution of the refractive index, n , for PbS nanocrystalline films of thicknesses 26, 34, 79 and 93 nm.

Fig.5.6 The real part of the dielectric constant, ϵ_1 , as a function of wavelength for PbS nanocrystalline films of thicknesses 26, 34, 79 and 93 nm.

Fig. 5.7 The straight line part of the relation between the real part of dielectric constant, ϵ_1 , and the wavelength squared, λ^2 , for PbS nanocrystalline thin films of thickness values 26, 34, 79, and 93 nm

Fig.5.8 The optical transmittance and reflectance spectra of PbTe nanocrystalline films with for thicknesses 21, 50 and 66 nm.

Fig.5.9 The spectral distribution of the absorption coefficient, α , of PbTe nanocrystalline films of thicknesses 21, 50 and 66 nm.

Fig. 5.10 The relationship between $(\alpha h\nu)^2$ and $h\nu$ for PbTe films.

Fig.5.11 The spectral distribution of the refractive index, n , of PbTe nanocrystalline films of thicknesses 21, 50 and 66 nm

Fig. 5.12 The spectral distribution of the real part of the dielectric constant with the wavelength, λ , for PbTe nanocrystalline films of thicknesses 21, 50 and 66 nm.

Fig. 6.1 Frequency dependence of the ac conductivity at different temperatures for PbS and PbTe.

Fig. 6.2 Dependence of the activation energy on the applied frequency.

Fig. 6.3 Frequency dependence of dielectric constant (ϵ') at different temperatures for PbS and PbTe.

Fig. 6.4 Frequency dependence of dielectric loss (ϵ'') at different temperatures for PbS and PbTe.

Fig. 6.5 Frequency dependence of the real part of electric modulus (M') at different temperatures for PbS and PbTe.

Fig. 6.6 Frequency dependence of the imaginary part of electric modulus (M'') at different Fig. 6.7 Plot of (M''/M''_{\max}) versus (f/f_{\max}) for PbS and PbTe.

Fig.6.8 The variation of the electrical resistivity of PbTe thin films of thicknesses 21,50 and 66 nm with temperature

Figure 6.9 The variation of the charge carriers concentration with temperature for PbTe thin films.

Fig.6.10 The variation of charge carriers mobility of PbTe thin films with temperature increase

Fig.6.11 The variation of the electrical resistivity with temperature for PbS films of thickness of thickness 93 nm

Fig.6.12 The variation of the charge carriers concentration with temperature for PbS films of thickness 93 nm is shown in Fig.6.12

Fig.6.13 Charge carriers mobility variation with heating of PbS films of thickness 93 nm.

Fig 6.14 I-V characteristics of the Au/p-PbS/n-Si/Al heterojunction in the temperature range 298 – 378 K.

Fig. 6.15 semi logarithmic forward $\ln I - V$ relationship of the Au/p-PbS/n-Si/Al heterojunction.

Fig.6.16 relationship between the ideality factor, m , and the heating temperature of the Au/p-PbS/n-Si/Al heterojunction.

Fig 6.17 Variation of the barrier potential with heating temperature for Au/p-PbS/n-Si/Al heterojunction.

Fig. 6.18 Relation between the ideality factor, m , and the barrier potential height, ϕ_b , of the Au/p-PbS/n-Si/Al heterojunction.

Fig. 6.19 The plot of ΔV versus I for Au/p-PbS/n-Si/Al heterojunction.

Fig. 6.20 Electrical series resistance for the Au/p-PbS/n-Si/Al heterojunctions as a function of heating temperature.

Fig 6.21 I-V characteristics of the Au/p-PbTe/n-Si/Al heterojunction in the temperature range 298 – 378 K.

Fig. 6.22 semi logarithmic forward $\ln I - V$ relationship of the Au/p-PbTe/n-Si/Al heterojunction

Fig.6.23 Relationship between the ideality factor, m , and the heating temperature of the Au/p-PbTe/n-Si/Al heterojunction.

Fig 6.24 Variation of the barrier potential with heating temperature for Au/p-PbTe/n-Si/Al heterojunction.

Fig. 6.25 Relation between the ideality factor, m , and the barrier potential height, ϕ_b , of the Au/p-PbTe/n-Si/Al heterojunction.

Fig. 6.26 The plot of ΔV versus I for Au/p-PbTe/n-Si/Al heterojunction.

Fig. 6.27 Electrical series resistance for the Au/p-PbTe/n-Si/Al heterojunctions as a function of heating temperature.